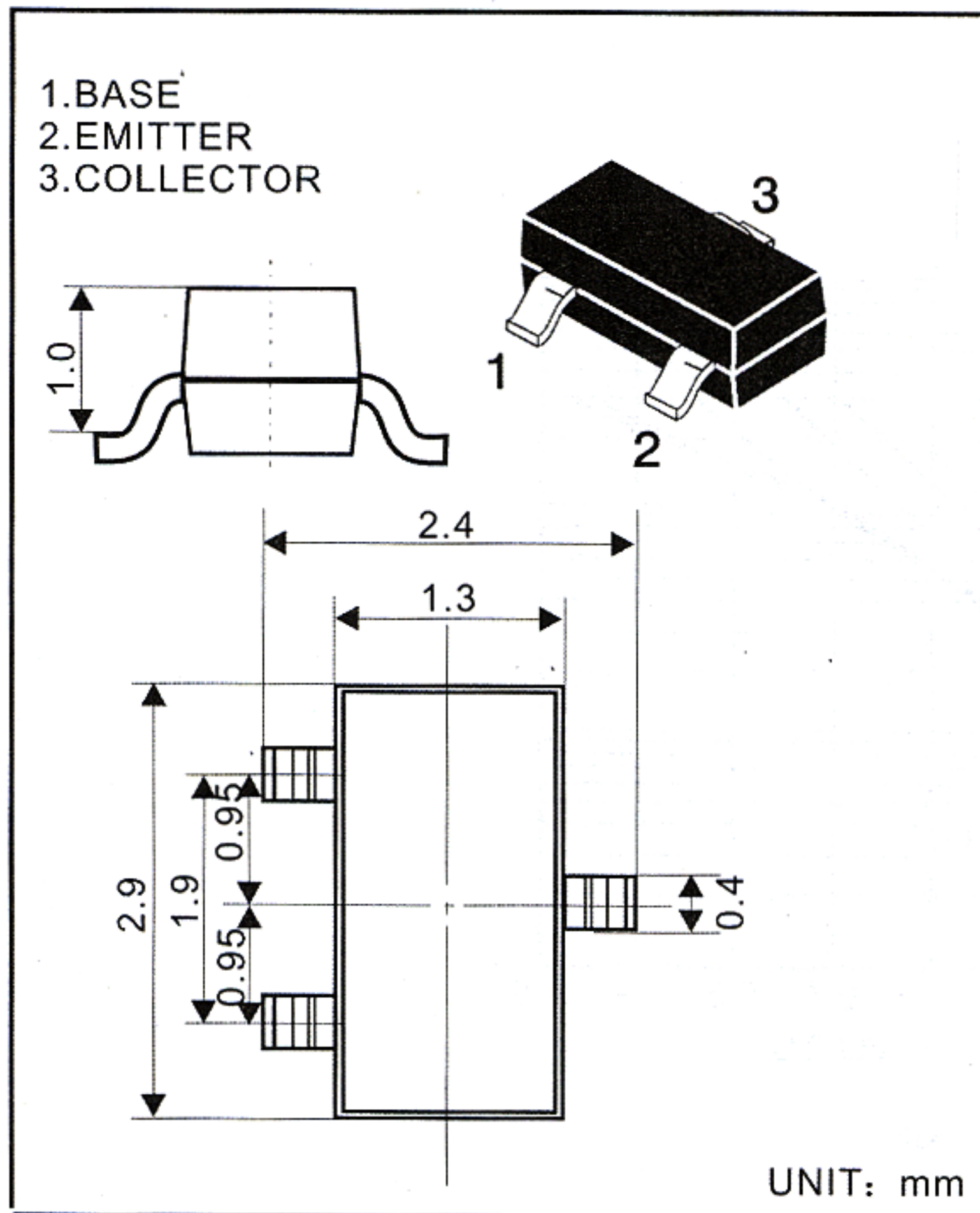


BAS70 SERIES SCHOTTKY DIODE



FEATURES

Power dissipation

P_D : 200mW ($T_{amb}=25^{\circ}C$)

Forward current

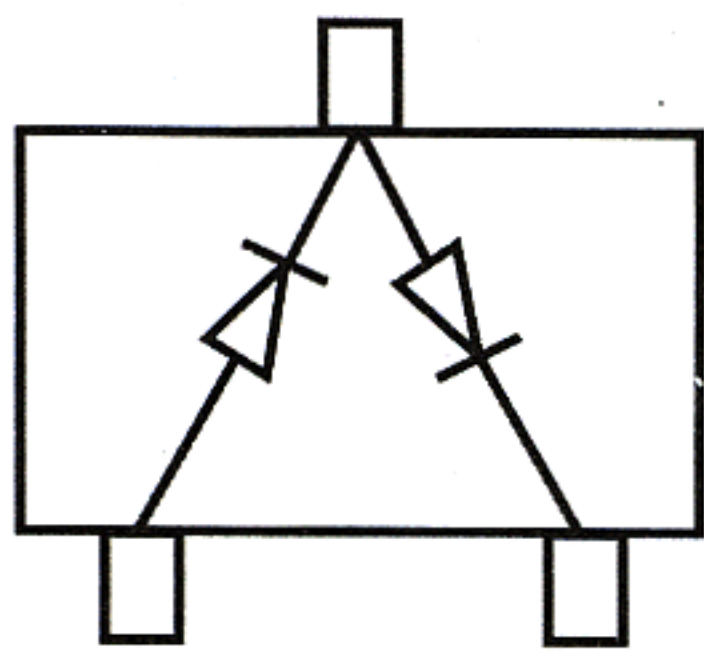
I_F : 200mA

Reverse voltage

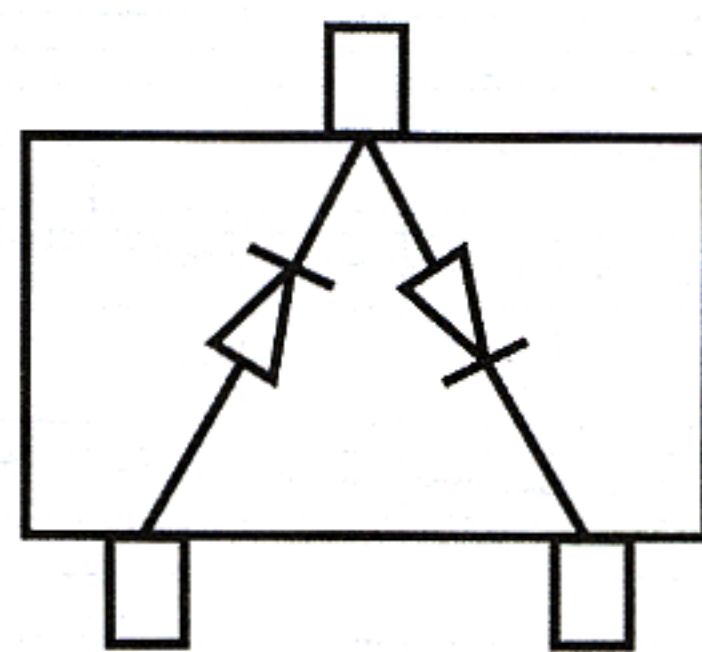
V_R : 70V

Operating and storage junction temperature range

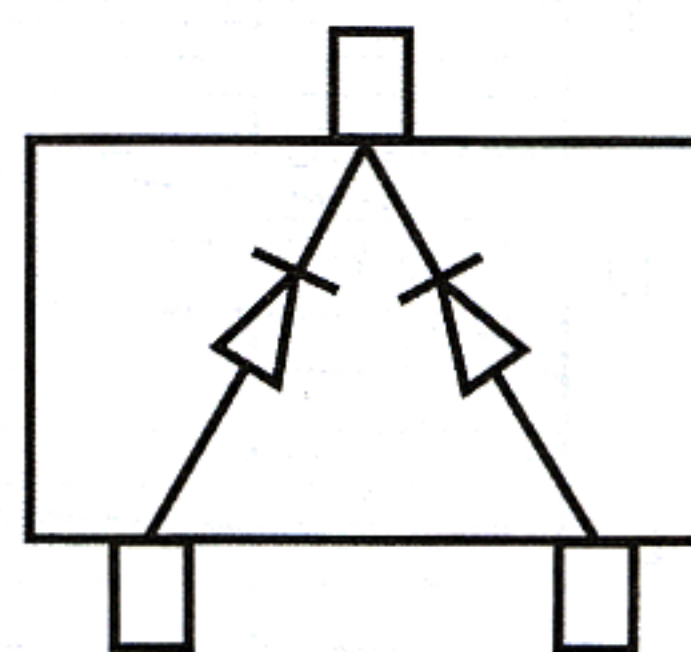
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



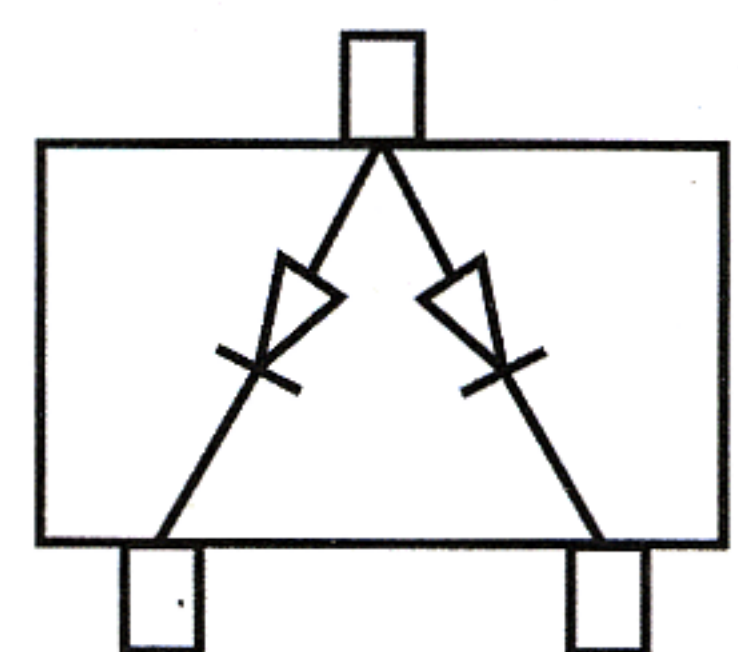
BAS70 MARKING: 73



BAS70-04 MARKING: 74



BAS70-05 MARKING: 75

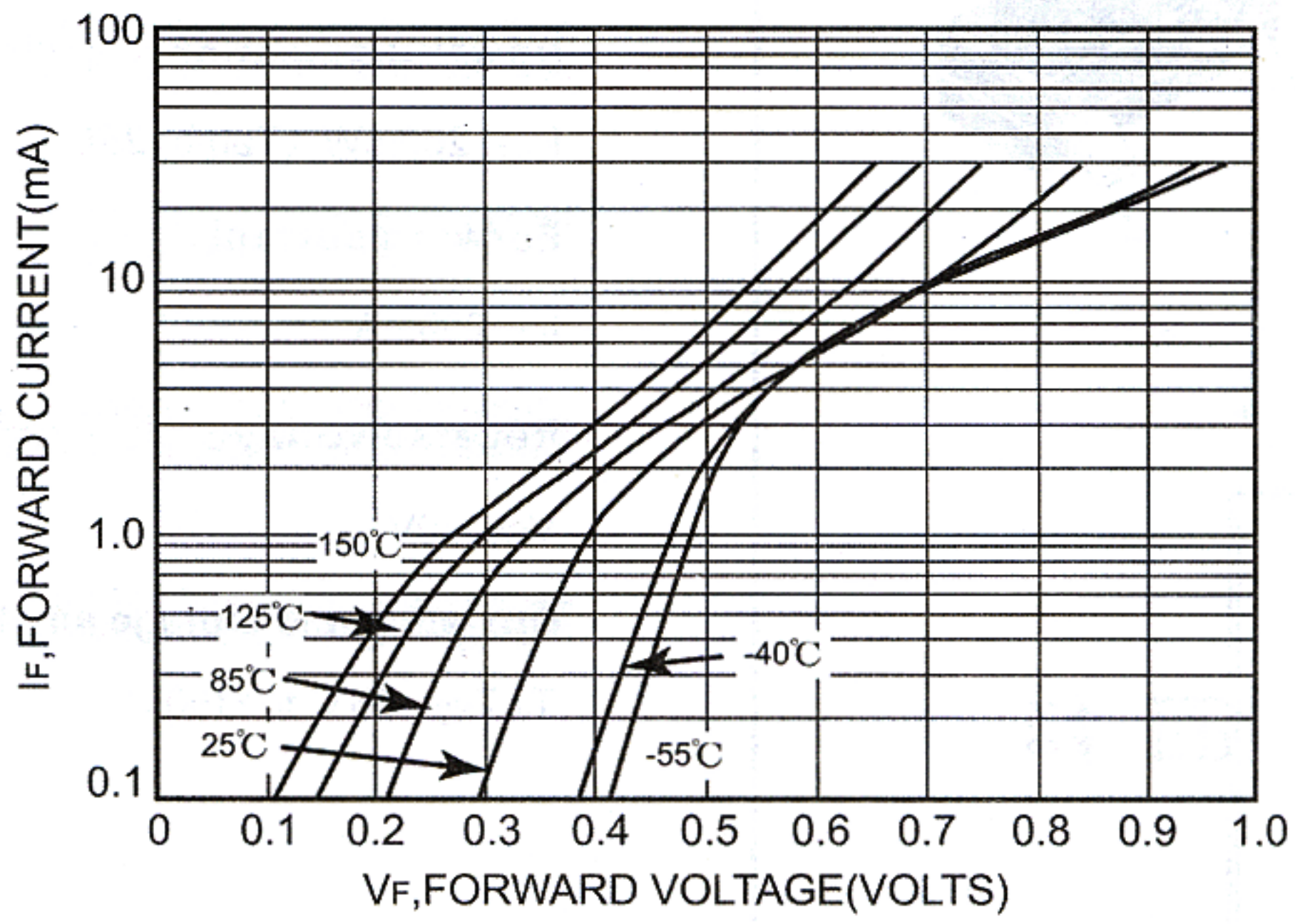


BAS70-06 MARKING: 76

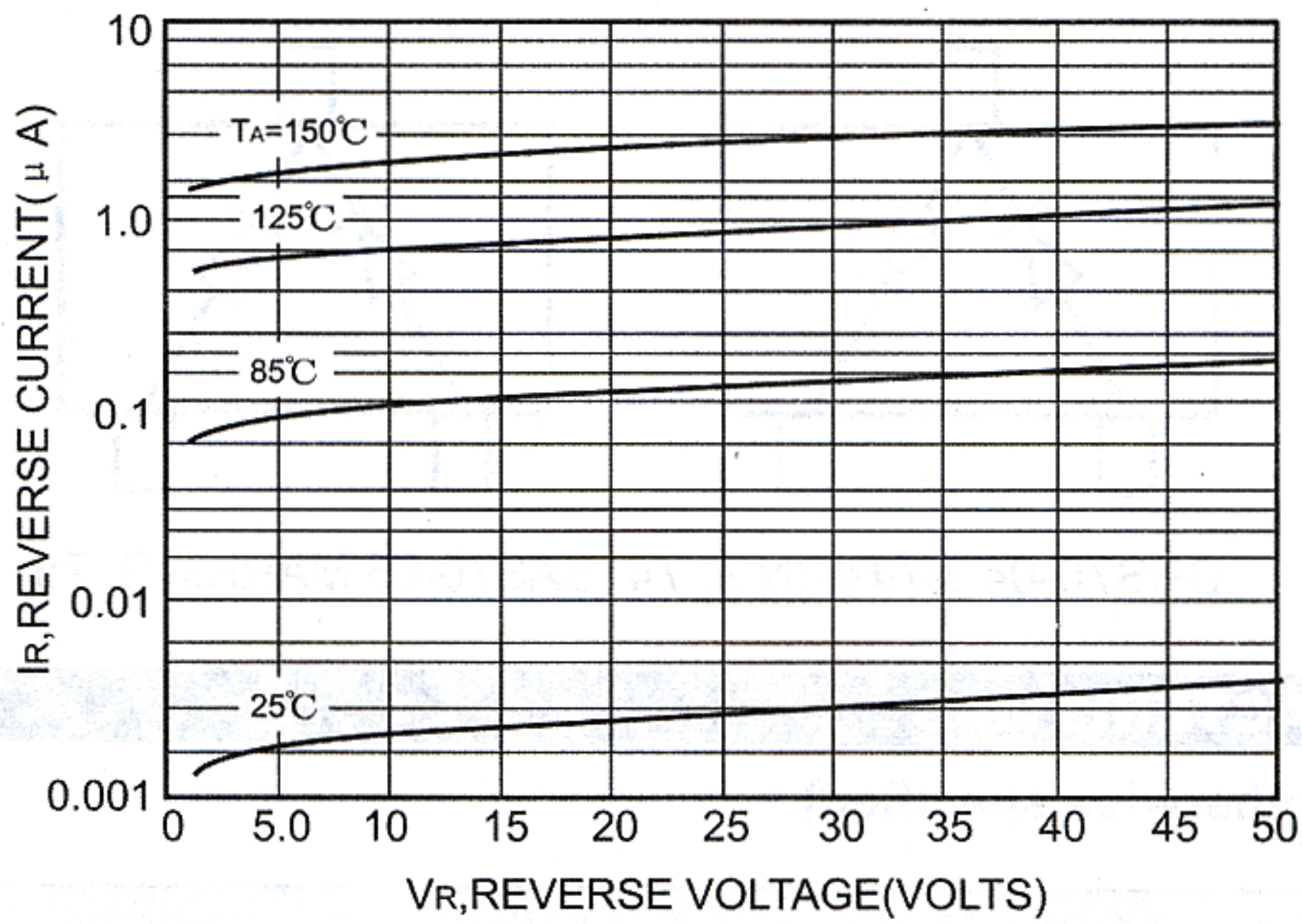
ELECTRICAL CHARACTERISTICS

($T_{amp}=25^{\circ}C$ unless otherwise specified)

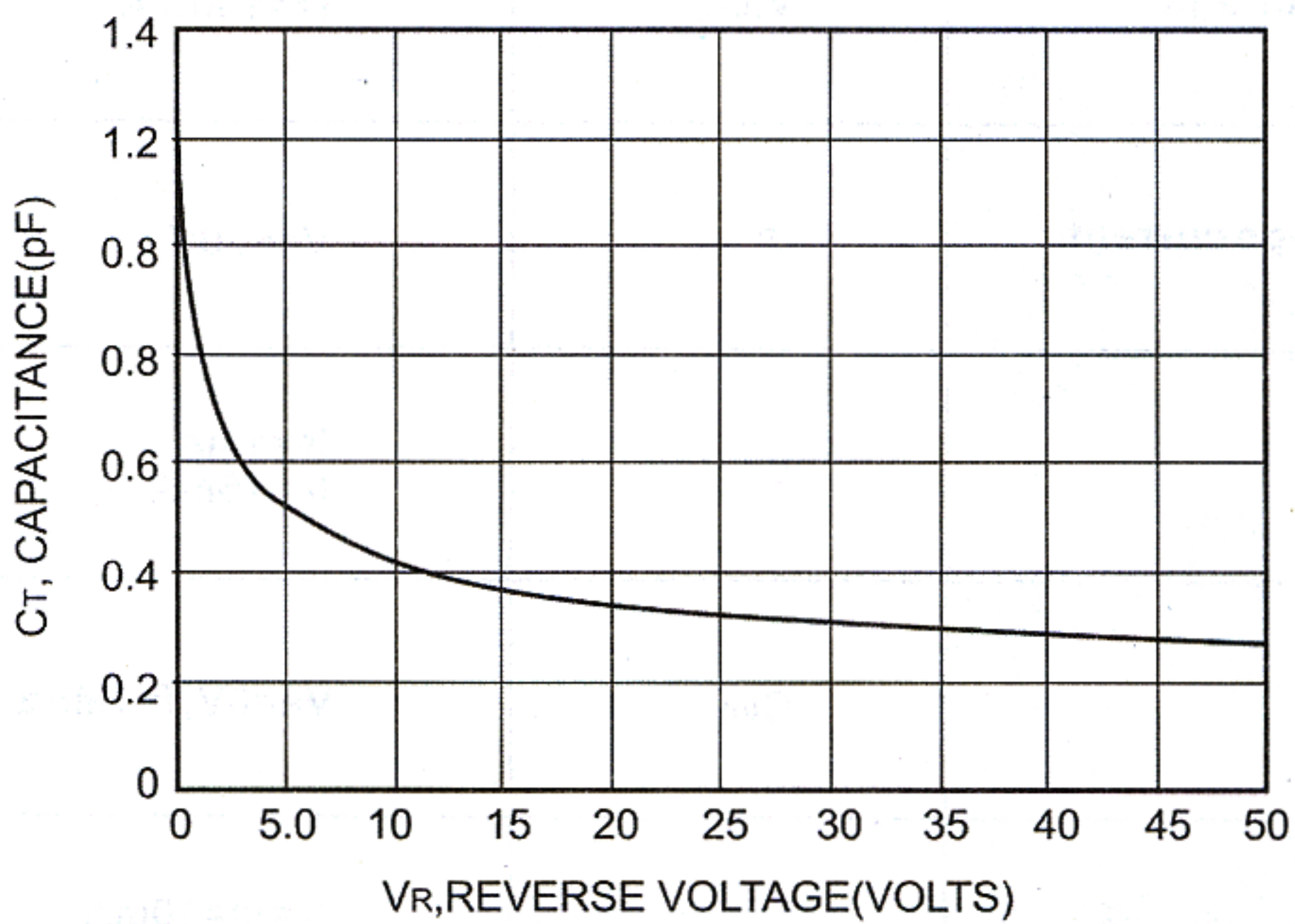
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	70		V
Reverse voltage leakage current	I_R	$V_R=50V$		100	nA
Forward voltage	V_F	$I_F=1mA$ $I_F=15mA$		410 1000	mV
Diode capacitance	C_{tot}	$V_R=0V, f=1MHz$		2	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10mA$ $I_{rr}=0.1 \times I_R$		5	ns



Forward Voltage



Reverse Current versus Reverse Voltage



Typical Capacitance